

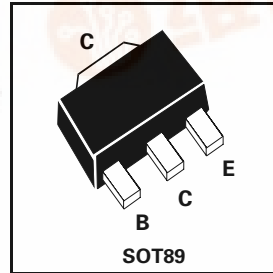
**SOT89 PNP SILICON PLANAR
MEDIUM POWER TRANSISTOR**

BCX5316

ISSUE 4 – MARCH 2001

COMPLIMENTARY TYPE – BCX5616

PARTMARKING DETAIL – AL



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	-100	V
Collector-Emitter Voltage	V_{CEO}	-80	V
Emitter-Base Voltage	V_{EBO}	-5	V
Peak Pulse Current	I_{CM}	-1.5	A
Continuous Collector Current	I_C	-1	A
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1	W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-65 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown voltage	$V_{(BR)CBO}$	-100			V	$I_C = -100\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-80			V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5			V	$I_E = -10\mu A$
Collector Cut-Off Current	I_{CBO}			-0.1 -20	μA μA	$V_{CB} = -30V$ $V_{CB} = -30V, T_{amb} = 150^{\circ}C$
Emitter Cut-Off Current	I_{EBO}			-10	μA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$			-0.5	V	$I_C = -500mA, I_B = -50mA^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$			-1.0	V	$I_C = -500mA, V_{CE} = -2V^*$
Static Forward Current Transfer Ratio	h_{FE}	25 100 25		250		$I_C = -5mA, V_{CE} = -2V^*$ $I_C = -150mA, V_{CE} = -2V^*$ $I_C = -500mA, V_{CE} = -2V^*$
Transition Frequency	f_T	150			MHz	$I_C = -50mA, V_{CE} = -10V,$ $f = 100MHz$
Output Capacitance	C_{obo}			25	pF	$V_{CB} = -10V, f = 1MHz$

*Measured under pulsed conditions.